MOOV

NSR-2205i12D TEST SHEET

(6" Reticle , 22mm Field 8" Notch Wafer)

No	Item	Specification	Result				Condition	Remark
1	Exposure Power	700㎽/㎠ or more	Normal		775.866 ㎽/㎠		On the wafer surface when replacing the lamp SLOT 1 : Conv. **NA=0.63**	
2	Illumination Uniformity	Within ± 1.5%	Normal		1.49%		Within exposure range: 3 times of measurement	
3	Intergrated Exposure Stability	50 ㎽/㎠ or more Within ±1.0% 100 ㎽/㎠ Within ±0.5%	Time (ms)	Specification (mJ/㎠)	Read Value (mJ/㎠)	Result (%)	(1)Input time : 100msec (2)Input time : 200msec (3)Input time : 400msec (4)Input time : 800msec 10 measurements	
			100	49.5 ~ 50.5	49.9	**-0.20**		
			200	99 ~ 101	99.8	**-0.20**		
			400	198 ~ 202	199.5	**-0.25**		
			800	396 ~ 404	398.9	**-0.28**		
4	Wafer Holder Flatness	Within 2.0㎛ / 200㎜	Max - Min		**1.5 ㎛**		Max: 0.670 Min : -0.830	
5	Leveling Setting Accuracy	Within ± 1.0sec	X:-0.269, Y:-0.066, R:0.694, P:-0.237				Measurement 10 time	
6	Auto Focus Repeatability	(Max-min/2)Within ± 0.10㎛	0.082 ㎛				1 wafer 10 times shot center measurement	
7	Reticle Blind Setting Accuracy	+0.4 to +0.8㎜ (on reticle)	Xp		**0.65**		1 Wafer, shot measurement	
			Xm		**0.6**			
			Yp		**0.6**			
			Ym		**0.65**			
8	Reticle Rotation	|X| ≤ 0.02㎛ 3σ ≤ 0.02㎛	**Absolute value 0.007 ㎛**				5 times of measurement	
			Repeatability 0.002 ㎛					
9	Array Orthogonality	Within ±0.1 sec	**0.082 sec(0.39 urad)**				After soft correction	
10	Stepping Precision	NORMAL ±0.045㎛ (3σ)	3 Sigma				SMCP : 228STEP	
			x	**0.015 ㎛**	y	**0.015 ㎛**		
11	Lens Distortion (Including Magnification error)	Within ±0.055㎛	Max				SLOT1 Conv. : **Lens NA=0.63**	
			Xmax	**0.022 ㎛**	Ymax	**0.046 ㎛**		
			Min					
			Xmin	**-0.045 ㎛**	Ymin	**-0.013 ㎛**		
12	LSA Telecen	Within ±3㎛	X	**1.82**	Y	**0.94**	Correction after measurement with software	
13	FIA Telecen	Within ±3㎛	X	**1.25**	Y	**-0.68**	Correction after measurement with software	
14	Overlay-LSA	|X|+3σ≤0.065㎛(shot center+4 corners)	X	**0.027 ㎛**	Y	**0.035 ㎛**	Overlay in resist image	
15	Overlay-FIA	|X|+3σ≤0.065㎛(shot center+4 corners)	X	**0.056 ㎛**	Y	**0.063 ㎛**		
16	Focus Calibration repeatability	Within 0.15㎛	**0.09㎛**				Nikon test reticle 20 measurements	
17	Wafer Prealignment repeatability	X Y T 3σ≤15㎛	**X: 3.1㎛,Y: 5.8 ㎛,T: 7.2 ㎛,Y-T: 18.6 ㎛**				Same wafer 20 measurements X,Y,Θ,Y-Θ, independent evaluation	Measure only 0 degrees 90 degree correction
18	Open Flame (Max.Exposure Area)	22.0 X 25.2mm	**OK**				1 wafer, shot measurement	
19	Field Inclination	Max-Min Within 0.35㎛	**0.345 ㎛**				91° 0.35μm H&V H/V SLOT 1 : Conv.**NA=0.63**	
		AST Within 0.35㎛	**-0.135 ㎛**					
20	Magnification Control	Within ± 0.020㎛	**Focus : -0.057um** **Mag : 0.002um**				INIT,HEAT 150、COOL 180 SLOT 1 : Conv. **NA=0.63**	
21	Montion Test	Reticle All slot	**All Slot load/unload**				(1)Reticle 10 Slot	
		Wafer 200ea	**wafer 200 ea OK**				(1) Continuous exposure of 200 wafers	